

Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	6.0	$^{\circ}C/W$
Thermal resistance, junction - ambient	R_{thJA}	-	-	70	$^{\circ}C/W$
Soldering temperature, wave soldering for 10s	T_{sold}	-	-	265	$^{\circ}C$

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	30			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	1.2	1.7	2.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = 30V, V_{GS} = 0V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 20A$				
		$V_{GS} = 4.5V, I_D = 10A$				
Forward Transconductance	g_{FS}	$V_{DS} = 25V, I_D = 4A$				
Source-drain voltage	V_{SD}	$I_S = 20A$				

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	$f = 1MHz$	-	675	-	pF
Output capacitance	C_{oss}		-	186	-	
Reverse transfer capacitance	C_{rss}		-	16	-	

Gate Charge characteristics ($T_a = 25$)



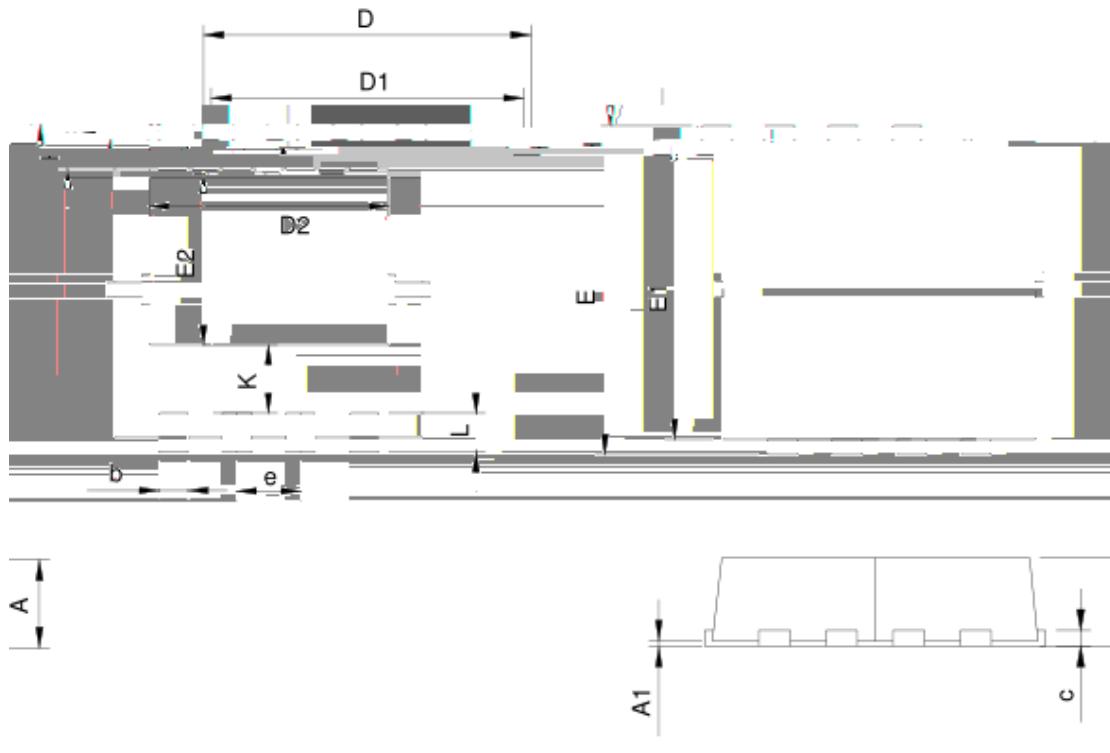
Body Diode Reverse Recovery Time trr IF=20A,
dI/dt=100A/μs 12





sions(DFN3x3)

Unit mm



DFN3.3x3.3-8		RECOMMENDED LAND PATTERN			
		MILLIMETERS		INCHES	
		MIN.	MAX.	MIN.	MAX.
A	0.70	1.00	0.028	0.039	
A1	0.00	0.05	0.000	0.002	
b	0.25	0.35	0.010		
c	0.14	0.20	0.006		
D	3.10	3.50	0.122		
D1	3.05	3.25	0.120		
D2	2.35	2.55	0.093	0.100	
E	3.10	3.50	0.122	0.138	
E1	2.90	3.10	0.114	0.122	
E2	2.35	2.55	0.093	0.100	
e	0.65 BSC			0.026 BSC	
H	0.32	0.52	0.013	0.020	
K	0.59	0.79	0.023	0.031	
	0.25	0.35	0.010	0.022	